



SiC Bridge Rectifier

SKM125KD12SC

Features*

- Full Silicon Carbide (SiC) power module
- 1200V SiC Schottky FWDs
- High frequency rectifier
- Improved thermal performances with Aluminium Nitride (AlN) substrate
- UL recognized, file no. E63532

Typical Applications

- Rectifiers for DC/DC converters
- High frequency rectifier applications

Remarks

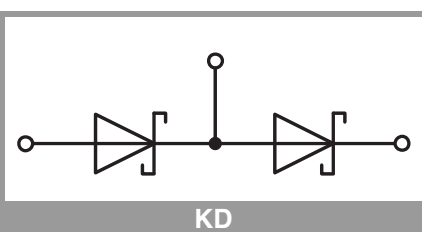
- Case temperature limited to $T_C=125^{\circ}\text{C}$
- Recommended $T_{jop} = -40...+150^{\circ}\text{C}$

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Diode 1				
V _{RRM}	T _j = 25 °C		1200	V
I _F	T _j = 175 °C	T _c = 25 °C	264	A
		T _c = 80 °C	200	A
I _{Fnom}			180	A
I _{FSM}	10 ms, sin 180°, T _j = 150 °C		630	A
i ² t	10 ms, sin 180°, T _j = 150 °C		1984	A ² s
T _j			-40 ... 175	°C

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Module			
$I_{t(RMS)}$		500	A
T_{stg}	module without TIM	-40 ... 125	$^{\circ}\text{C}$
V_{isol}	AC sinus 50 Hz, $t = 1$ min	4000	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Diode 1					
V_F	$I_F = 180$ A	$T_j = 25^{\circ}\text{C}$	1.36	1.55	V
	chipelevel	$T_j = 150^{\circ}\text{C}$	1.70	1.98	V
V_{F0}	chipelevel	$T_j = 25^{\circ}\text{C}$	0.95	1.05	V
		$T_j = 150^{\circ}\text{C}$	0.80	0.90	V
r_F	chipelevel	$T_j = 25^{\circ}\text{C}$	2.3	2.8	m Ω
		$T_j = 150^{\circ}\text{C}$	5.0	6.0	m Ω
C_j	$V_R = 800$ V, $f = 1$ MHz, $T_j = 25^{\circ}\text{C}$		0.840		nF
Q_c	$V_R = 800$ V, $di/dt_{off} = 500$ A/ μs , $T_j = 25^{\circ}\text{C}$		0.67		μC
$R_{th(j-c)}$	per diode			0.215	K/W

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Module						
L _{CE}			15			nH
R _{CC'+EE'}	measured per switch	T _C = 25 °C	0.55			mΩ
		T _C = 125 °C	0.85			mΩ
R _{th(c-s)}	calculated without thermal coupling (λ _{grease} =0.81 W/(m*K))		0.02		0.038	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



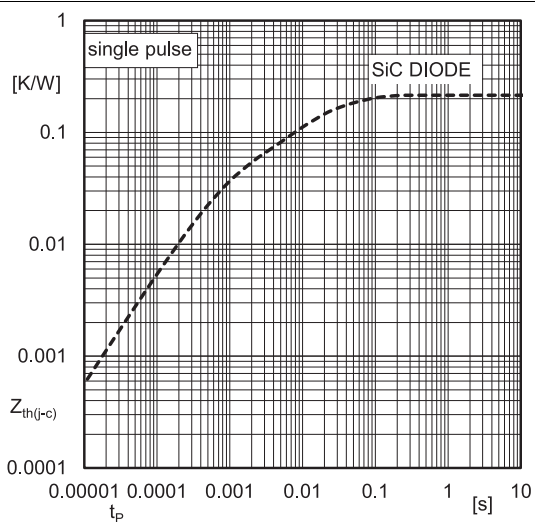


Fig. 9: Typ. transient thermal impedance

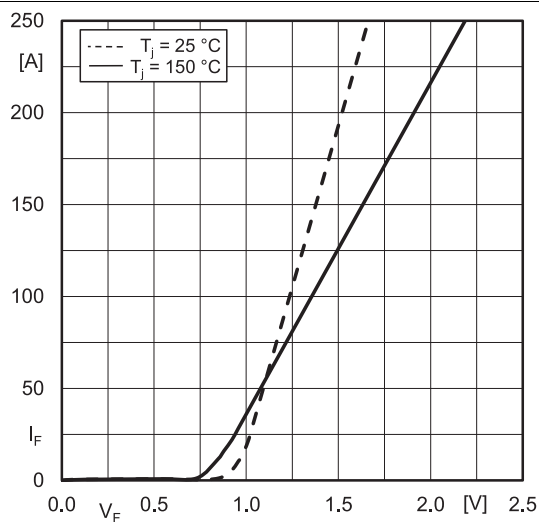


Fig. 10: Typ. Diode forward charact., incl. $R_{CC'+EE'}$

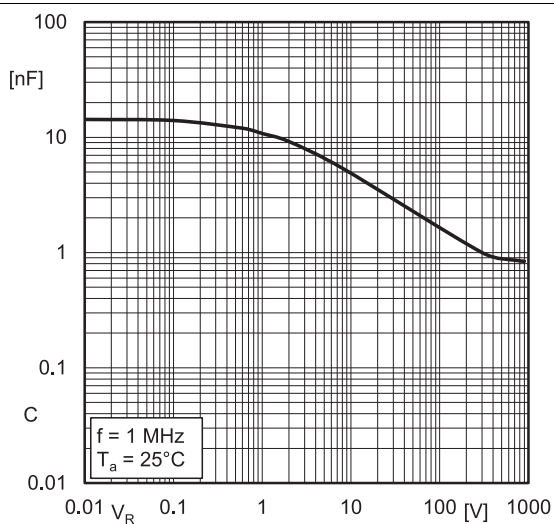
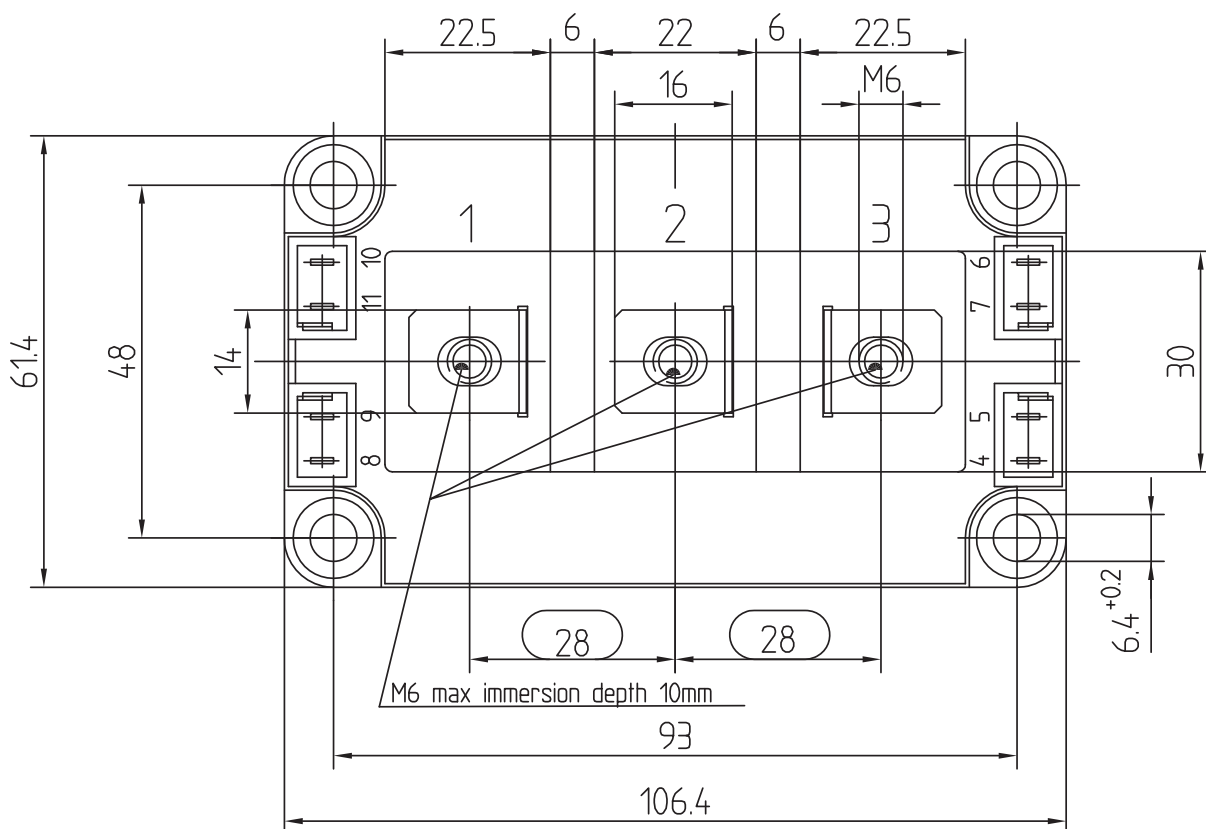
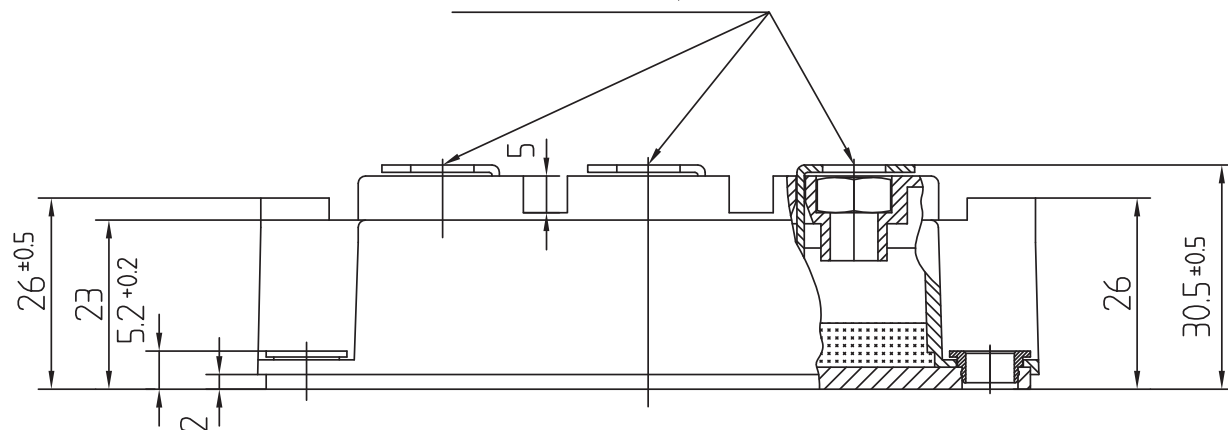


Fig. 20: Typ. Capacitance-voltage characteristic

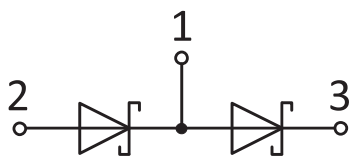
SKM125KD12SC

Dimension in mm

M6 max immersion depth 10mm



SEMITRANS 3



KD

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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